Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:	
Metal	
Overall Length:	
1.253 inches	
Overall Height:	
0.505 inches	
End Application:	
Thermal imagery - mc	tns
Mounting Facility Qu	iantity:
1	
Joint Electronic Dev	ice Engineering Council/jedec/case Outline Designation:
Do-4	
Electrode Internally-	electrically Connected To Case:
Cathode	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed ca	ase
Overall Width Acros	s Flats:
0.424 inches	
Thread Size:	
0.190 inches	
Semiconductor Mate	rial:
Silicon	
Voltage Rating In Vo	Its Per Characteristic:
40.0 breakdown volta	ge, collector-to-emitter, base open
Maximum Operating	Tempurature Per Measurement Point:
150.0 degrees celsius	case
Test Data Document	:
81349-mil-s-19500/30	4a specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in
specification format;	excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on
certain environmental	and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Desig	nator:
Unf	
Terminal Type And G	Quantity:
2 tab, solder lug	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	